



N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Typ)
30	0.0022 at V _{GS} = 10 V	90	82 nC
	0.0027 at V _{GS} = 4.5 V	90	

FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested

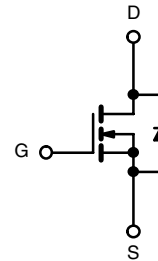
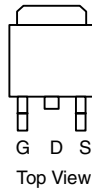


RoHS COMPLIANT

APPLICATIONS

- OR-ing
- Server

TO-263



Ordering Information: SUM90N03-2m2P-E3 (Lead (Pb)-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 175 °C)	I _D	T _C = 25 °C	90 ^{a, e}	
		T _C = 70 °C	90 ^e	
		T _A = 25 °C	33 ^{b, c}	
		T _A = 70 °C	29.8 ^{b, c}	
Pulsed Drain Current	I _{DM}	200	A	
Avalanche Current Pulse	I _{AS}	36		
Single Pulse Avalanche Energy	E _{AS}	64.8	V	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	90 ^{a, e}	
		T _A = 25 °C	3.13 ^{b, c}	
Maximum Power Dissipation	P _D	T _C = 25 °C	250 ^a	
		T _C = 70 °C	175	
		T _A = 25 °C	3.75 ^{b, c}	
		T _A = 70 °C	2.63 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	32	40	°C/W
Maximum Junction-to-Case	R _{thJC}	0.5	0.6	

Notes:

a. Based on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under Steady State conditions is 90 °C/W.

e. Calculated based on maximum junction temperature. Package limitation current is 90 A.



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-7.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.5		2.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	90			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 32\text{ A}$		0.0018	0.0022	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 29\text{ A}$		0.0022	0.0027	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 32\text{ A}$		160		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		12065		pF
Output Capacitance	C_{oss}			1725		
Reverse Transfer Capacitance	C_{rss}			970		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 32\text{ A}$		171	257	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 29\text{ A}$		81.5	123	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 29\text{ A}$		34		
Gate-Drain Charge	Q_{gd}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 29\text{ A}$		29		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.4	2.1	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.555\text{ }\Omega$ $I_D \cong 27\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		18	27	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(off)}$			70	105	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.625\text{ }\Omega$ $I_D \cong 24\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		55	83	
Rise Time	t_r			180	270	
Turn-Off Delay Time	$t_{d(off)}$			55	83	
Fall Time	t_f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			90	A
Pulse Diode Forward Current ^a	I_{SM}				200	
Body Diode Voltage	V_{SD}	$I_S = 22\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		52	78	ns
Body Diode Reverse Recovery Charge	Q_{rr}			70.2	105	nC
Reverse Recovery Fall Time	t_a			27		ns
Reverse Recovery Rise Time	t_b			25		

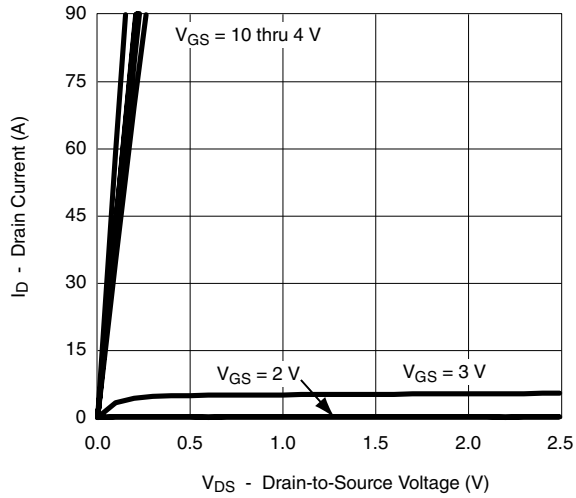
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

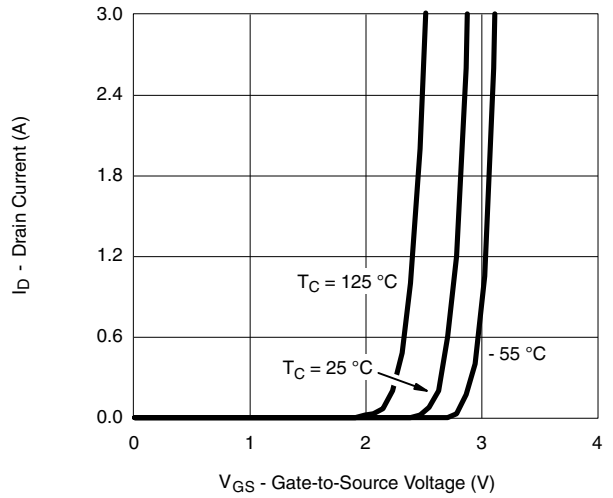
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



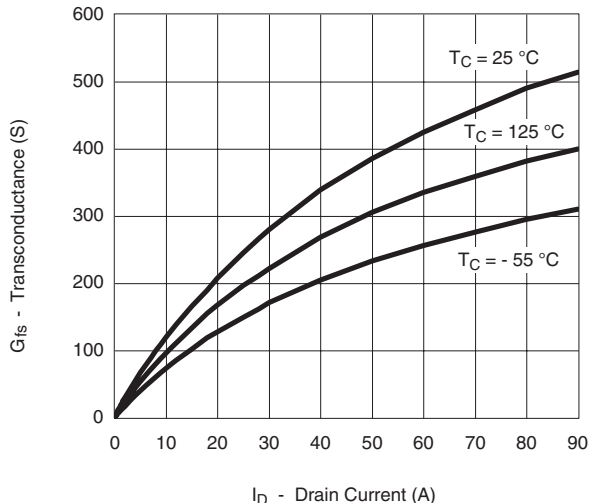
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



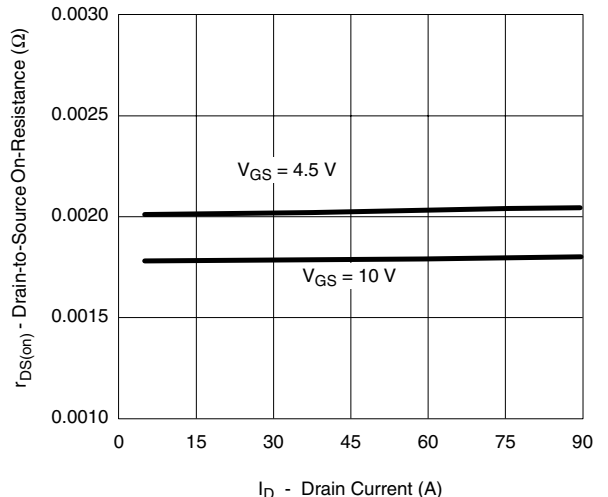
Output Characteristics



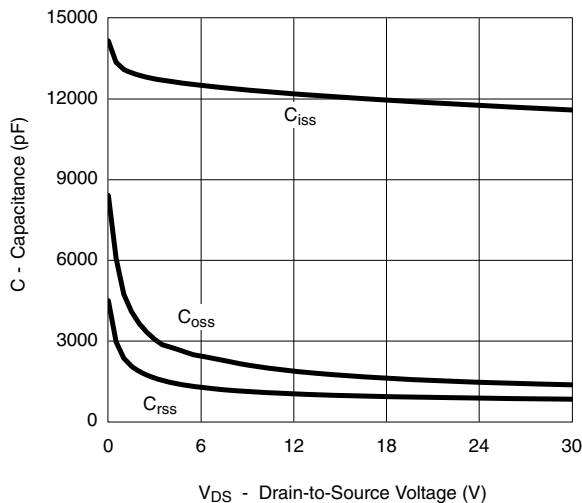
Transfer Characteristics



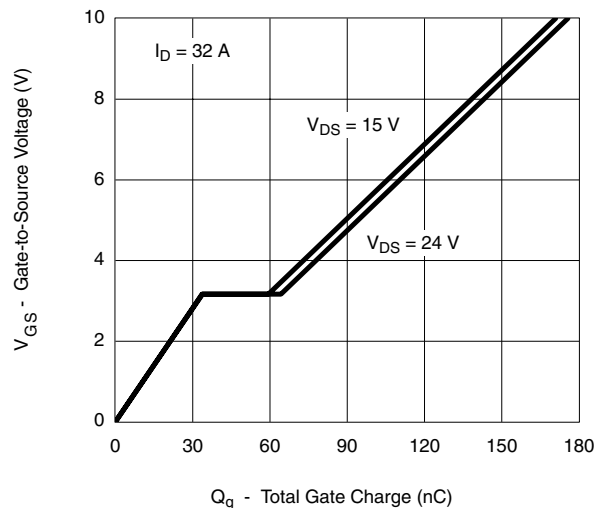
Transconductance



$r_{DS(on)}$ vs. Drain Current



Capacitance



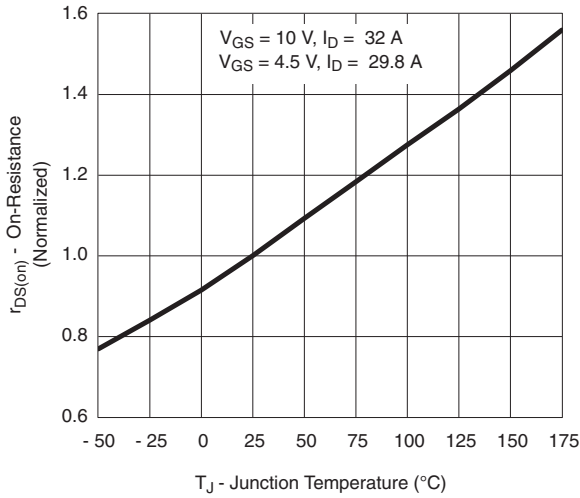
Gate Charge

SUM90N03-2m2P

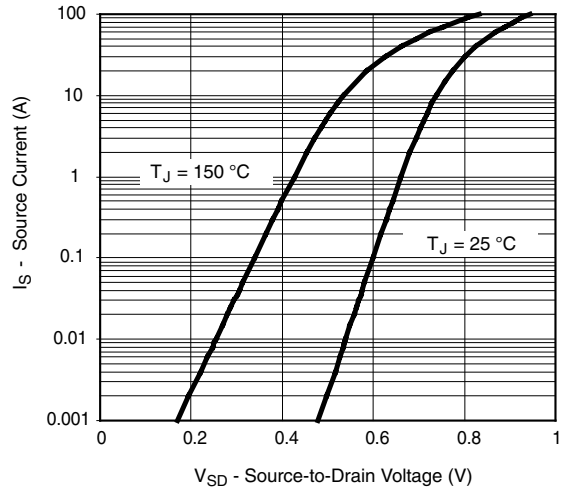


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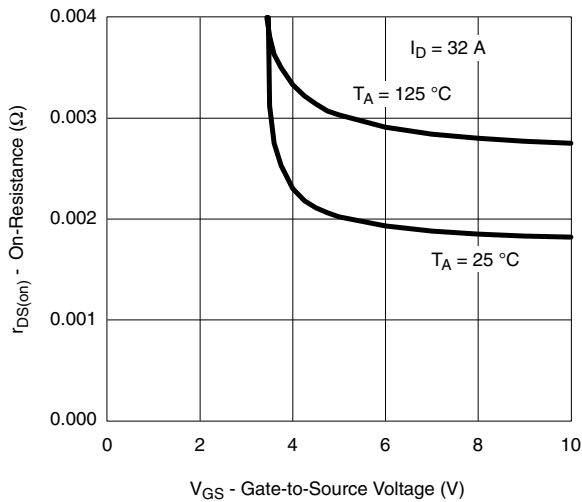
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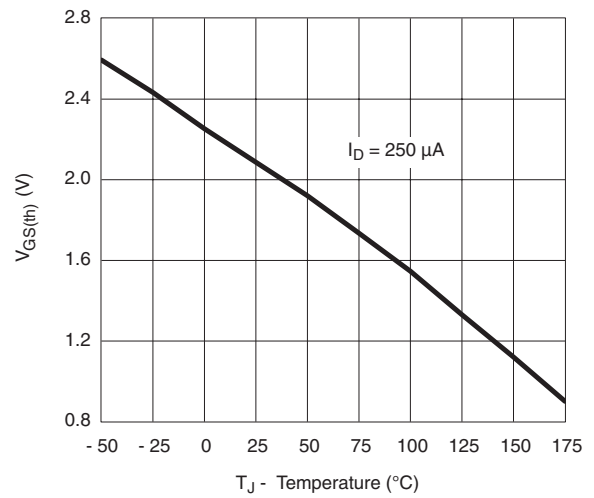
On-Resistance vs. Junction Temperature



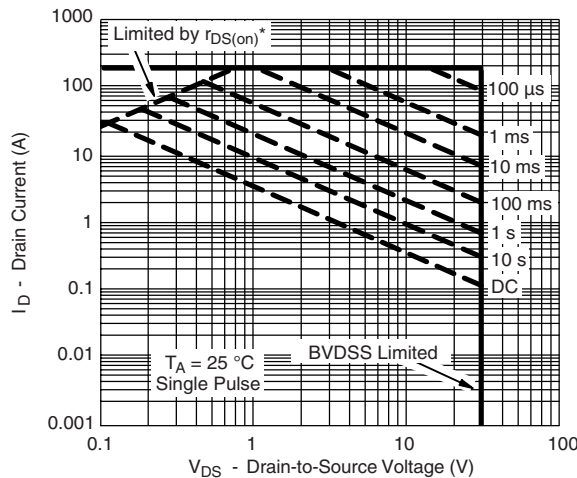
Forward Diode Voltage vs. Temperature



$r_{DS(on)}$ vs. V_{GS} vs. Temperature



Threshold Voltage

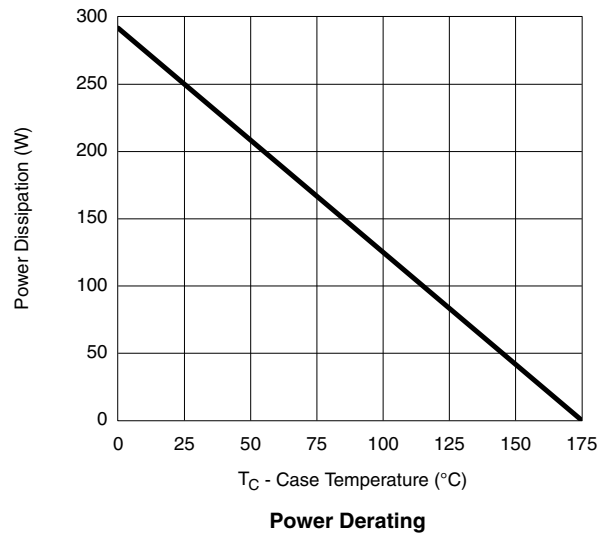
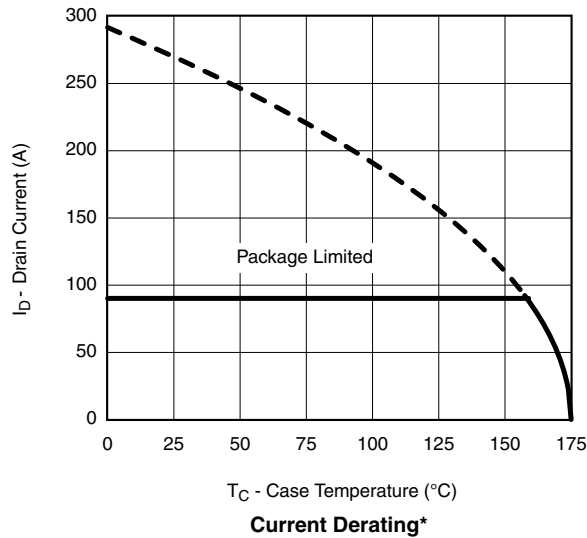


* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

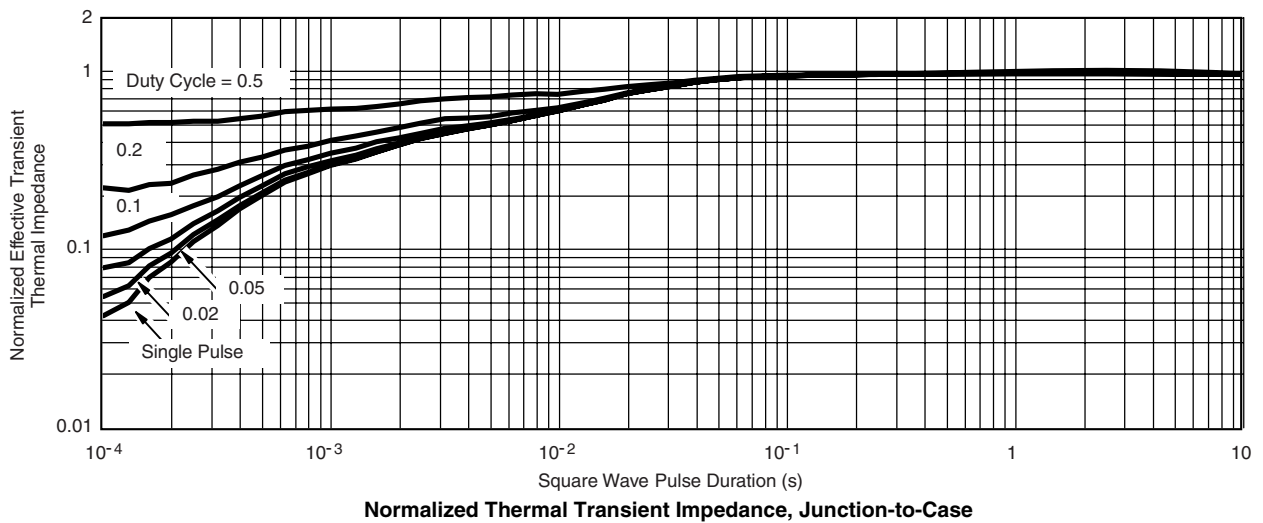
Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 175\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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